International
IOR Rectifier

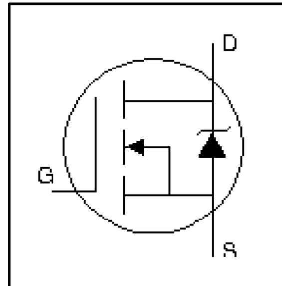
PD 9.1375

PRELIMINARY

IRL2910

HEXFET® Power MOSFET

- Logic-Level Gate Drive
- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated



V_{DSS} = 100V

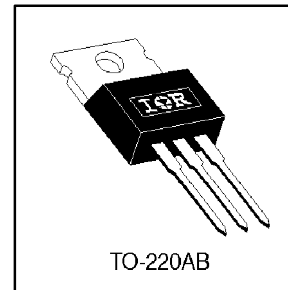
$R_{DS(on)}$ = 0.026Ω

I_D = 48A

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design for which HEXFET Power MOSFETs are well known, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.



TO-220AB

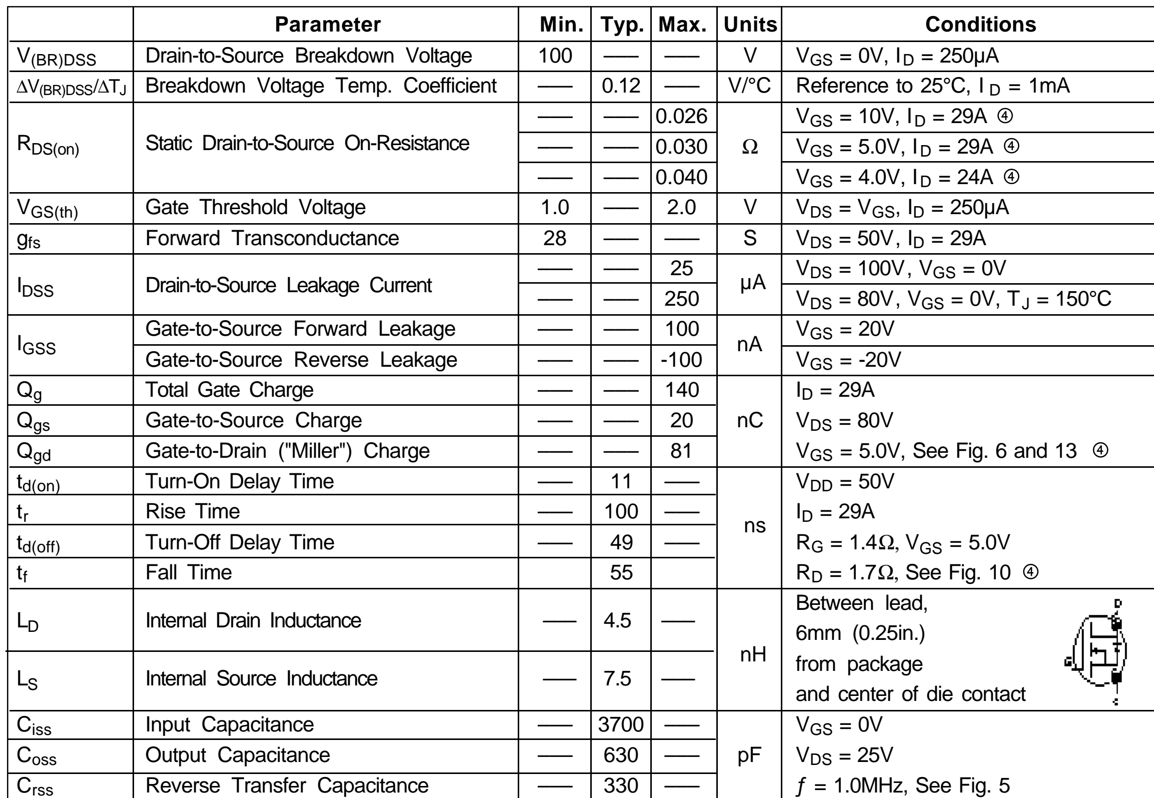
Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	48	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	34	
I_{DM}	Pulsed Drain Current ①	190	
P_D @T_C = 25°C	Power Dissipation	150	W
	Linear Derating Factor	1.0	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy ②	520	mJ
I_{AR}	Avalanche Current ①⑤	29	A
E_{AR}	Repetitive Avalanche Energy ①	15	mJ
dv/dt	Peak Diode Recovery dv/dt ③	7.4	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 srew	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	——	1.0	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	——	°C/W
$R_{\theta JA}$	Junction-to-Ambient	——	62	°C/W

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)



	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	100	——	——	V	V_{GS} = 0V, I_D = 250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	——	0.12	——	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	——	——	0.026	Ω	V_{GS} = 10V, I_D = 29A ④
		——	——	0.030		V_{GS} = 5.0V, I_D = 29A ④
		——	——	0.040		V_{GS} = 4.0V, I_D = 24A ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	——	2.0	V	V_{DS} = V_{GS}, I_D = 250μA
g_{fs}	Forward Transconductance	28	——	——	S	V_{DS} = 50V, I_D = 29A
I_{DSS}	Drain-to-Source Leakage Current	——	——	25	μA	V_{DS} = 100V, V_{GS} = 0V
		——	——	250		V_{DS} = 80V, V_{GS} = 0V, T_J = 150°C
I_{GSS}	Gate-to-Source Forward Leakage	——	——	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	——	——	-100		V_{GS} = -20V
Q_g	Total Gate Charge	——	——	140	nC	I_D = 29A
Q_{gs}	Gate-to-Source Charge	——	——	20		V_{DS} = 80V
Q_{gd}	Gate-to-Drain ("Miller") Charge	——	——	81		V_{GS} = 5.0V, See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	——	11	——	ns	V_{DD} = 50V
t_r	Rise Time	——	100	——		I_D = 29A
$t_{d(off)}$	Turn-Off Delay Time	——	49	——		R_G = 1.4Ω, V_{GS} = 5.0V
t_f	Fall Time		55			R_D = 1.7Ω, See Fig. 10 ④
L_D	Internal Drain Inductance	——	4.5	——	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	——	7.5	——		
C_{iss}	Input Capacitance	——	3700	——	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	——	630	——		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	——	330	——		ƒ = 1.0MHz, See Fig. 5

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	——	——	48	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	——	——	190		
V_{SD}	Diode Forward Voltage	——	——	1.3	V	T_J = 25°C, I_S = 29A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	——	240	350	ns	T_J = 25°C, I_F = 29A
Q_{rr}	Reverse Recovery Charge	——	1.8	2.7	μC	di/dt = 100A/μs ④

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② V_{DD} = 25V, starting T_J = 25°C, L = 1.2mH R_G = 25Ω, I_{AS} = 29A. (See Figure 12)

③ $I_{SD} \leq$ 29A, di/dt ≤ 490A/μs, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq$ 175°C

④ Pulse width ≤ 300μs; duty cycle ≤ 2%.

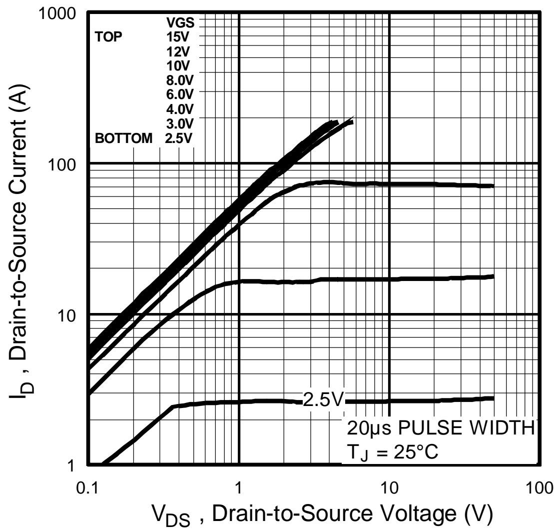


Fig 1. Typical Output Characteristics, $T_J = 25^oC$

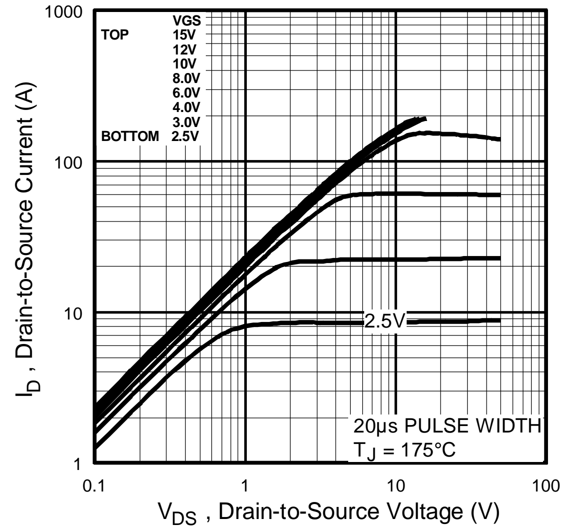


Fig 2. Typical Output Characteristics, $T_J = 175^oC$

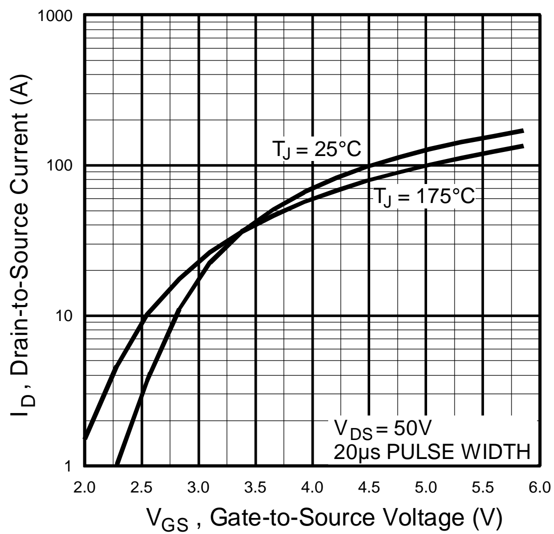


Fig 3. Typical Transfer Characteristics

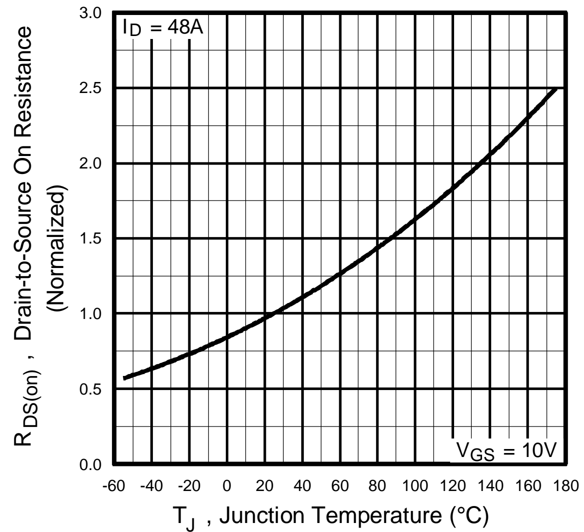


Fig 4. Normalized On-Resistance Vs. Temperature

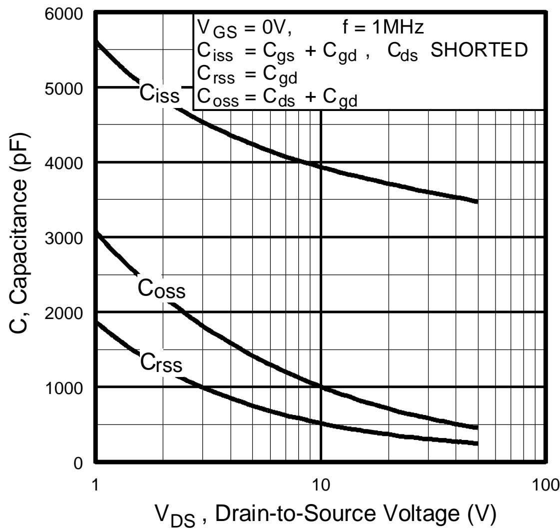


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

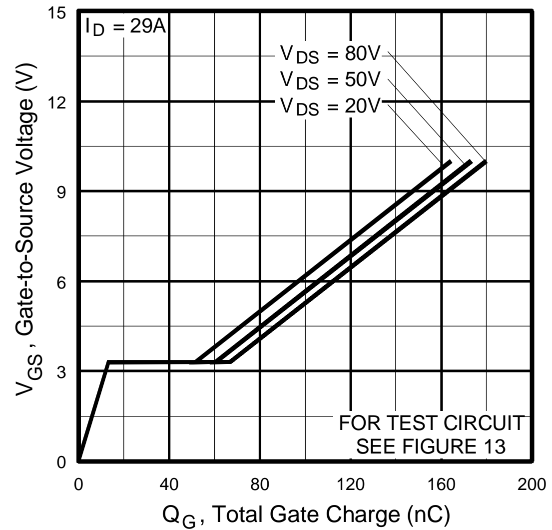


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

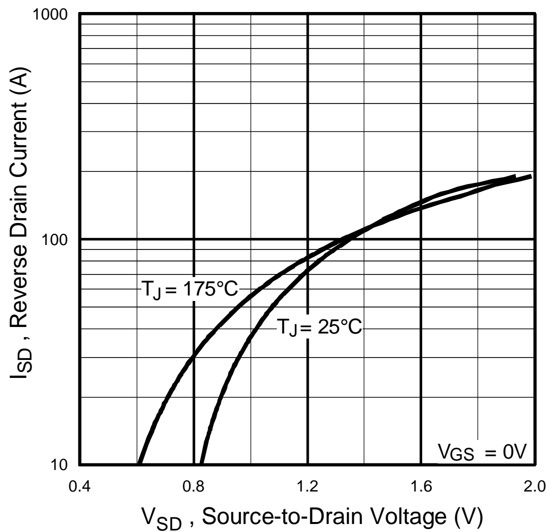


Fig 7. Typical Source-Drain Diode Forward Voltage

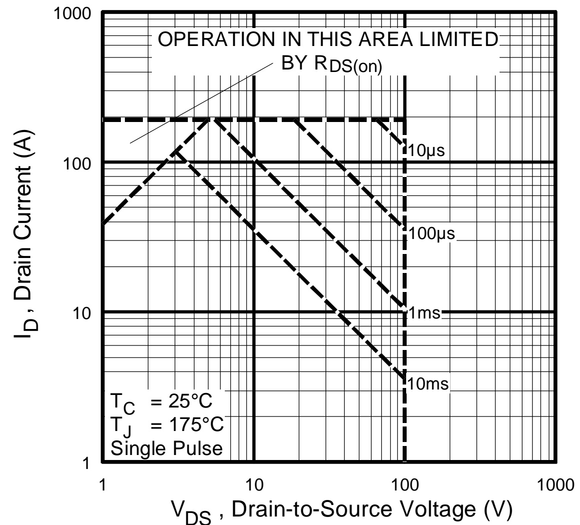


Fig 8. Maximum Safe Operating Area

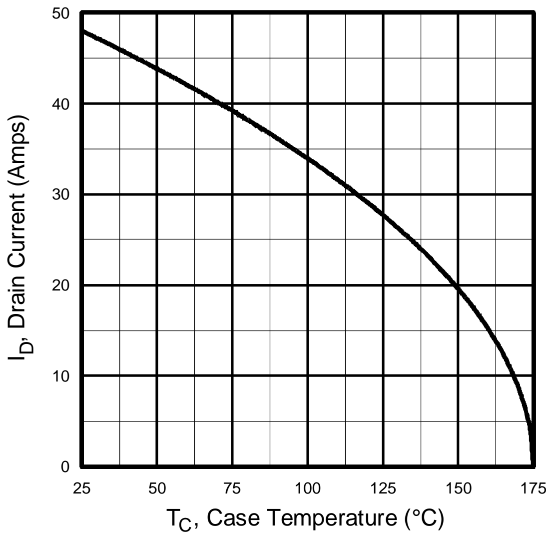


Fig 9. Maximum Drain Current Vs. Case Temperature

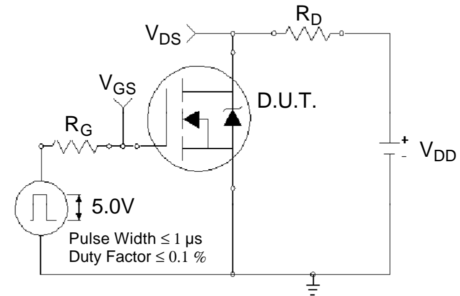


Fig 10a. Switching Time Test Circuit

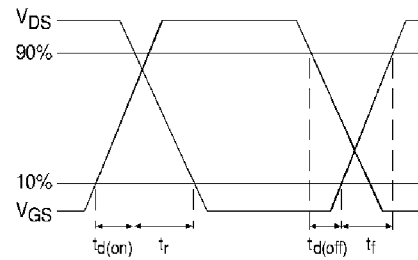


Fig 10b. Switching Time Waveforms

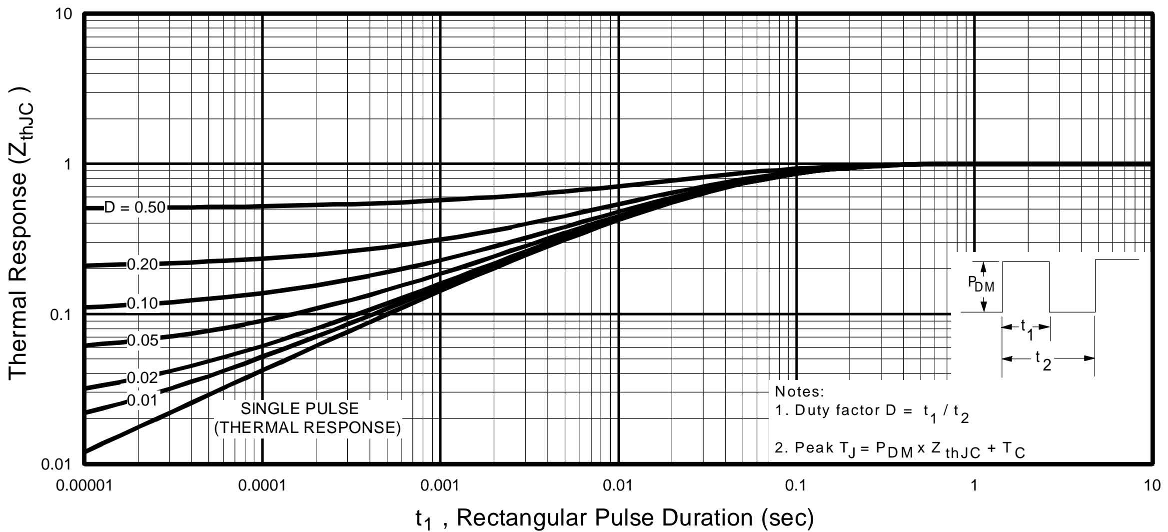


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

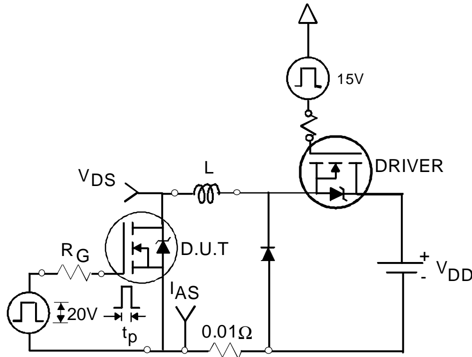


Fig 12a. Unclamped Inductive Test Circuit

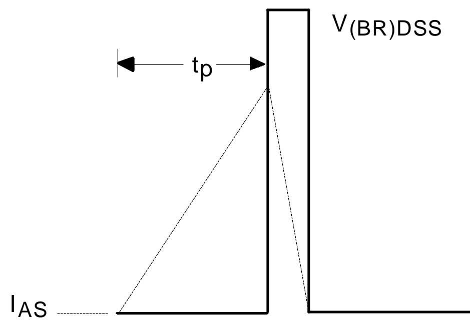


Fig 12b. Unclamped Inductive Waveforms

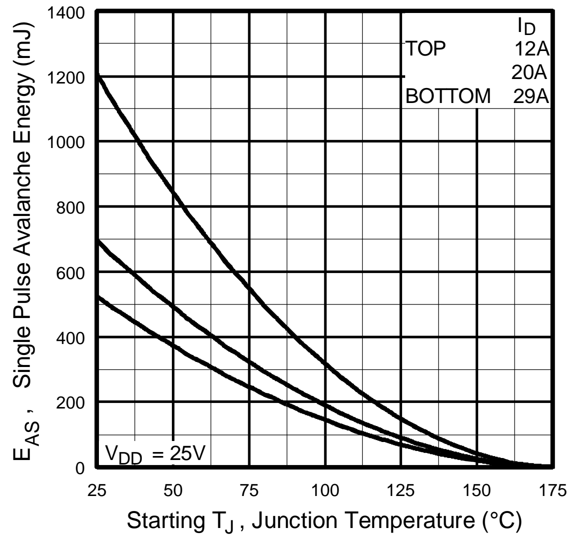


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

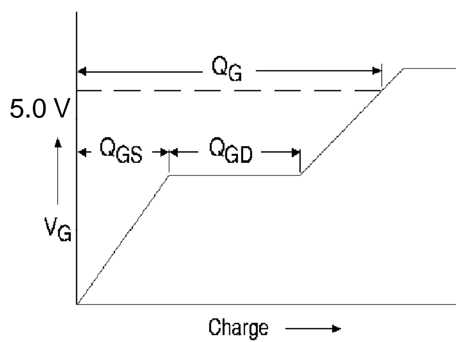


Fig 13a. Basic Gate Charge Waveform

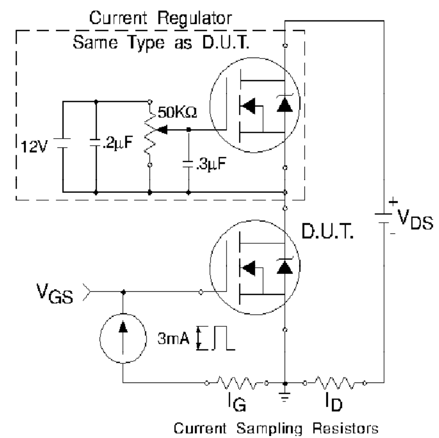
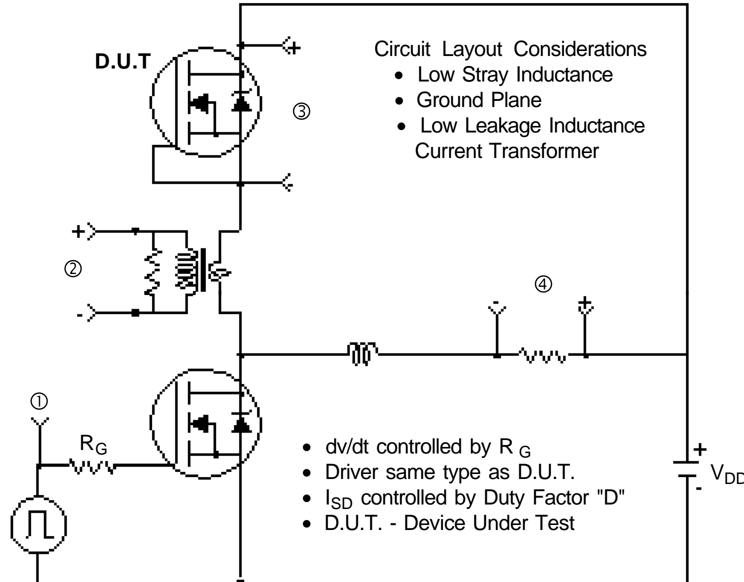
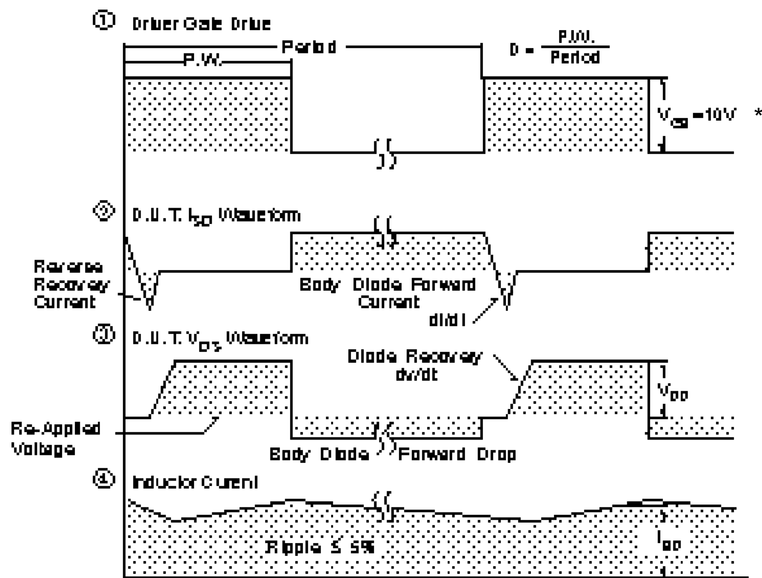


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit





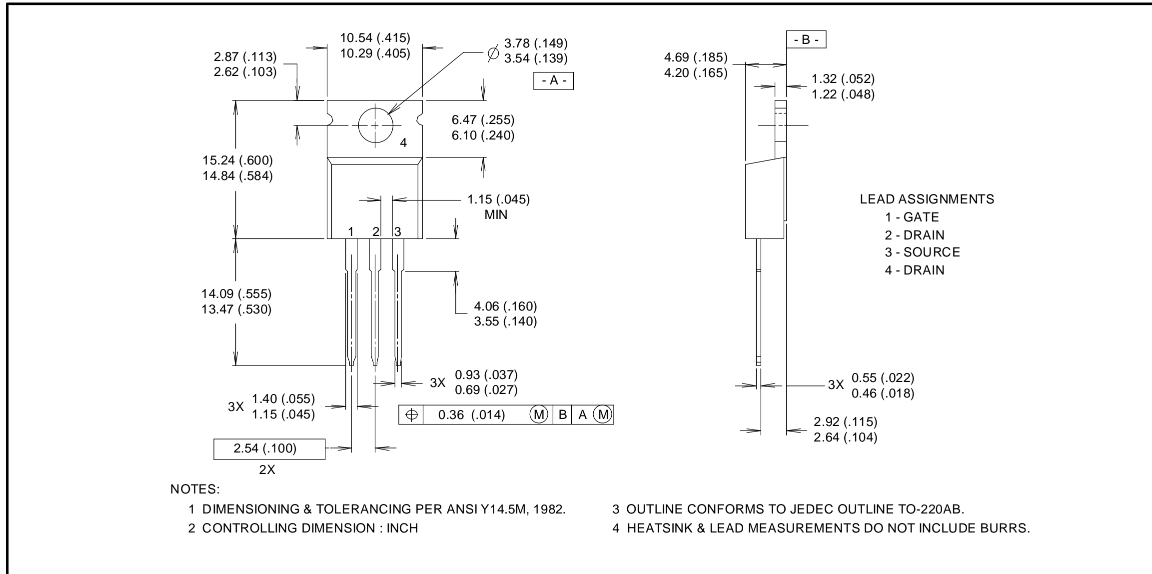
* V_{GS} = 5V for Logic Level Devices

Fig 14. For N-Channel HEXFETS

Package Outline

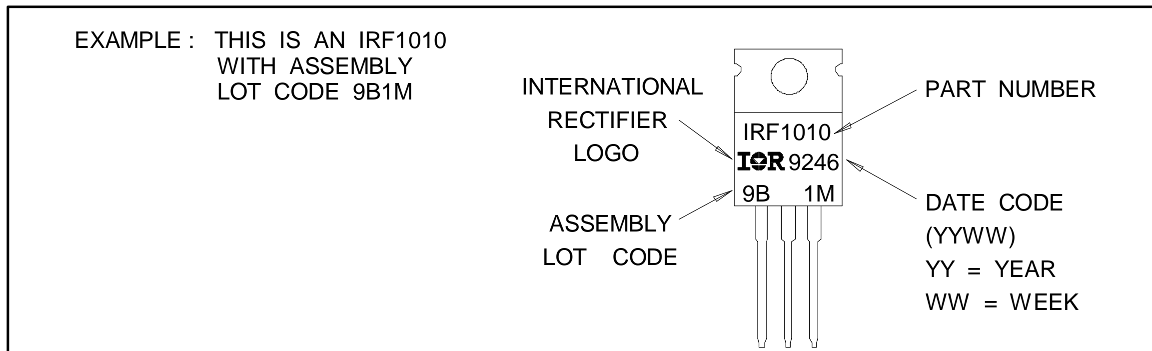
TO-220AB Outline

Dimensions are shown in millimeters (inches)



Part Marking Information

TO-220AB



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